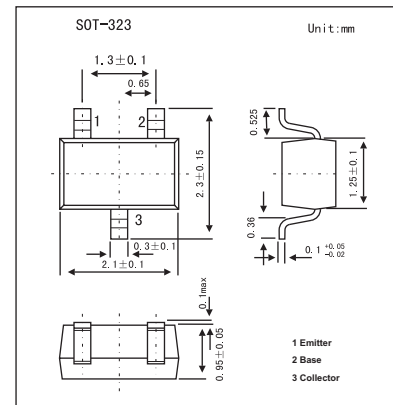


## High-frequency Amplifier Transistor

## 2SC4098

## ■ Features

- Low collector capacitance. (Cob : Typ. 1.3pF)
- Low rbb, high gain, and excellent noise characteristics.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	40	V
Collector-emitter voltage	V <sub>CEO</sub>	25	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>C</sub>	50	mA
Collector power dissipation	P <sub>C</sub>	0.2	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	BV <sub>CB0</sub>	I <sub>C</sub> =50μA	40			V
Collector-emitter voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA	25			V
Emitter-base voltage	BV <sub>EB0</sub>	I <sub>E</sub> =50μA	5			V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> =24V			0.5	μA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> =3V			0.5	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> /I <sub>B</sub> =10mA/1mA		0.1	0.3	V
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	82		180	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =6V, I <sub>E</sub> =-1mA, f=100MHz	150	300		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =6V, I <sub>E</sub> =0A, f=1MHz		1.3	2.2	pF

## ■ Marking

Marking	AP